# RENESAS

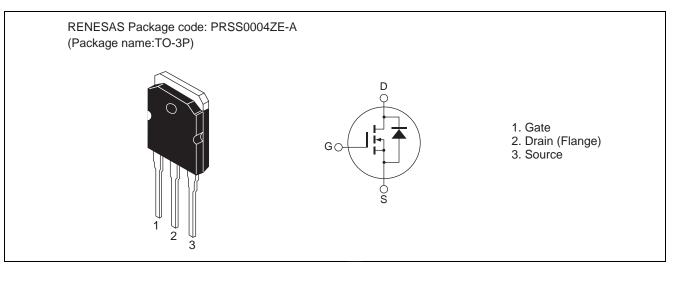
# RJK4515DPK

Silicon N Channel MOS FET High Speed Power Switching

# **Features**

- Low on-resistance  $R_{DS(on)} = 0.171 \ \Omega$  typ. (at  $I_D = 13.5 \ A$ ,  $V_{GS} = 10 \ V$ ,  $Ta = 25^{\circ}C$ )
- Low leakage current
- High speed switching

# Outline



# **Absolute Maximum Ratings**

			$(Ta = 25^{\circ}C)$
ltem	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	450	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub>	27	А
Drain peak current	Note1 I <sub>D (pulse)</sub>	81	А
Body-drain diode reverse drain current	I <sub>DR</sub>	27	А
Body-drain diode reverse drain peak current	Note1 I <sub>DR (pulse)</sub>	81	А
Avalanche current	I <sub>AP</sub> <sup>Note3</sup>	8	А
Avalanche energy	E <sub>AR</sub> <sup>Note3</sup>	3.6	mJ
Channel dissipation	Pch Note2	150	W
Channel to case thermal impedance	θch-c	0.833	°C/W
Channel temperature	Tch	150	٥°
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1 %

2. Value at  $Tc = 25^{\circ}C$ 

3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C

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# **Electrical Characteristics**

						(Ta = 25°C)
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	450	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	—	1	μΑ	$V_{DS} = 450 \text{ V}, \text{ V}_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±0.1	μΑ	$V_{GS}=\pm 30~V,~V_{DS}=0$
Gate to source cutoff voltage	V <sub>GS(off)</sub>	3.0	—	4.5	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Static drain to source on state resistance	R <sub>DS(on)</sub>	_	0.171	0.200	Ω	$I_D$ = 13.5 A, $V_{GS}$ = 10 V <sup>Note4</sup>
Input capacitance	Ciss		2600		pF	$V_{DS} = 25 V$ $V_{GS} = 0$ $f = 1 MHz$
Output capacitance	Coss		283		pF	
Reverse transfer capacitance	Crss	_	34	_	pF	
Turn-on delay time	t <sub>d(on)</sub>	_	40	—	ns	I <sub>D</sub> = 13.5 A
Rise time	tr	_	65	—	ns	$V_{GS} = 10 V$ $R_L = 16.7 Ω$ Rg = 10 Ω
Turn-off delay time	t <sub>d(off)</sub>	_	103	—	ns	
Fall time	t <sub>f</sub>	_	52	—	ns	
Total gate charge	Qg	—	61.8	—	nC	V <sub>DD</sub> = 360 V
Gate to source charge	Qgs	—	13.0	—	nC	V <sub>GS</sub> = 10 V I <sub>D</sub> = 27 A
Gate to drain charge	Qgd	—	27.5	—	nC	
Body-drain diode forward voltage	V <sub>DF</sub>	_	0.92	1.50	V	$I_F = 27 \text{ A}, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery time	t <sub>rr</sub>		360	_	ns	$I_F = 27 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 4. Pulse test

# Package Dimensions

Package Name TO-3P	JEITA Package Code SC-65	RENESAS Code PRSS0004ZE-A	Previous Code TO-3P / TO-3PV	MASS[Typ.] 5.0g	
	<u>1.6</u> <u>1.4 Ma</u>	$ \begin{array}{c} 15.6 \pm 0.3 \\ \phi 3.2 \pm 0.2 \\ \phi 3.2 \pm 0$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	4.8 ± 0.2 1.5 0.6 ± 0.2	Unit: mm
	<u>5.45 ± (</u>		<u>2</u> <u>.0</u> <u>1</u> <u>5.45 ± 0.5</u>		

# **Ordering Information**

Part No.	Quantity	Shipping Container
RJK4515DPK-00-T0	360 pcs	Box (Tube)

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